

IN THE SPECIFICATION

Page 1, amend paragraph 3 as follows:

A cobalt layer 120 is sputtered over the structure. A titanium layer 130 is sputtered on cobalt 120 to protect the cobalt layer from oxygen and other impurities during subsequent processing. Then the wafer is heated (in a rapid thermal processing step, or RTP) to react cobalt 120 with the silicon at the top of gate 100 and on source/drain regions 101. A cobalt silicide layer 210 (Fig. 2) forms as a result. This layer may include cobalt monosilicide CoSi and cobalt disilicide CoSi₂. Titanium 130 and the unreacted cobalt are removed with a wet etch. The wafer is heated again to increase the proportion of cobalt disilicide CoSi₂ in layer 210 and thus reduce the layer 210 resistivity. See H. Li Liu et al., "Gaseous Impurities in Co Silicidation", Journal of The Electrochemical Society, 148 (6) G344-G354 (2001), incorporated herein by reference.

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